

## PSMN8R7-80PS

# N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220 Rev. 02 — 1 November 2010 Product data

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	80	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>		-	-	90	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{ or } 100 \text{ or } $		-	-	14	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ constant}}$	[1]	-	7.5	8.7	mΩ
Dynamic ch	naracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$		-	11	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>		-	52	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(\text{init})} = 25 \text{ °C;} \\ &I_D = 90 \text{ A; } V_{sup} \leq 80 \text{ V;} \\ &R_{GS} = 50  \Omega; \text{ unclamped} \end{split}$		-	-	120	mJ

<sup>[1]</sup> Measured 3 mm from package.



### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		<sub>G</sub> (EA)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R7-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$	-	64	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	90	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	361	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	170	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	90	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	361	Α
Avalanche ru	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 90 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	120	mJ

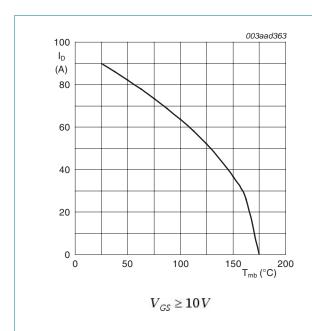
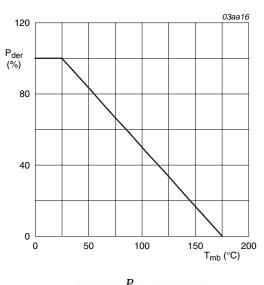


Fig 1. Continuous drain current as a function of mounting base temperature



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$ 

Fig 2. Normalized total power dissipation as a function of mounting base temperature

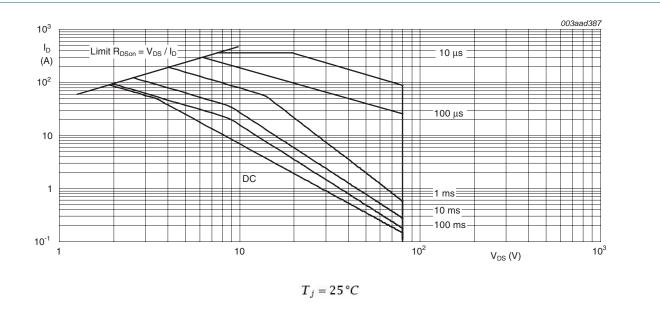


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.54	0.88	K/W

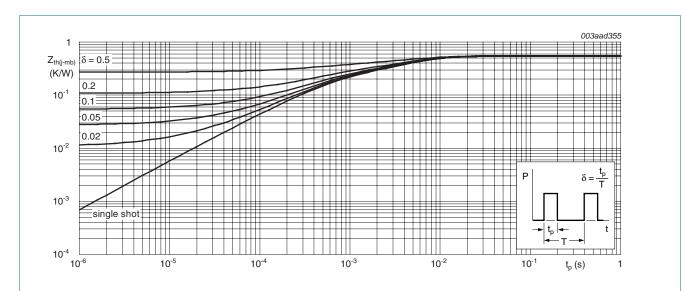


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2.3	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	5	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	-	20.8 8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	14	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	[1] -	7.5	8.7	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	44	-	nC
		$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ;	-	52	-	nC
$Q_{GS}$	gate-source charge	see Figure 14; see Figure 15	-	15	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ;	-	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge	see Figure 14	-	5.8	-	nC
$Q_{GD}$	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 40 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 40 \text{ V}$ ; see Figure 15	-	4.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3346	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	296	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	158	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_L$ = 1.6 $\Omega$ ; $V_{GS}$ = 10 V;	-	21	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	46	-	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 17</u>	-	0.79	1.2	V

**Table 6. Characteristics** ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ;	-	42	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	-	66	-	nC

#### [1] Measured 3 mm from package.

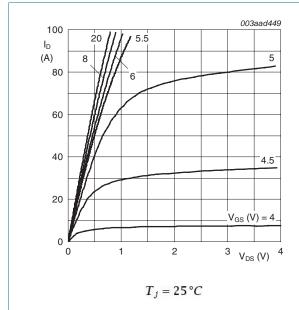


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

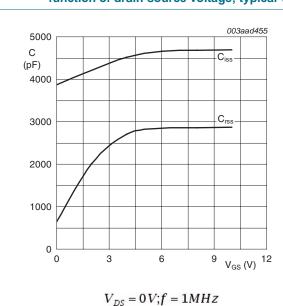


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

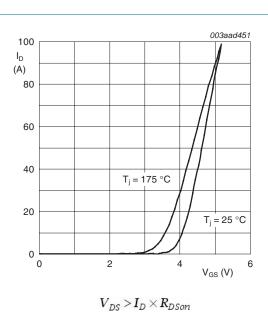


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

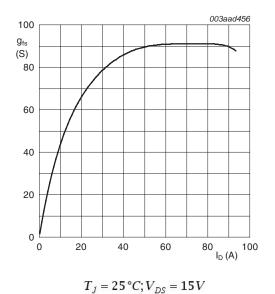


Fig 8. Forward transconductance as a function of drain current; typical values

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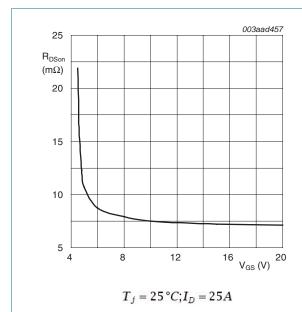


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

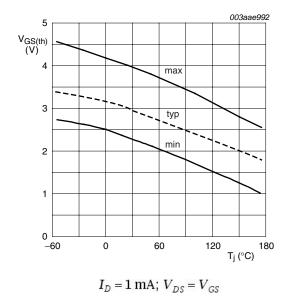


Fig 10. Gate-source threshold voltage as a function of junction temperature

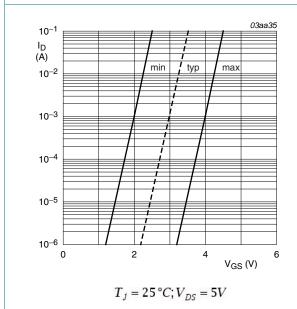


Fig 11. Sub-threshold drain current as a function of gate-source voltage

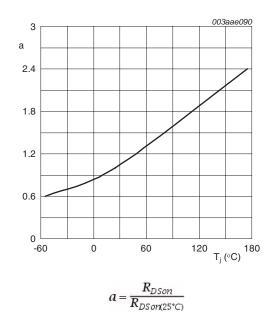


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

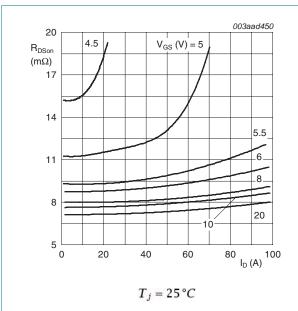
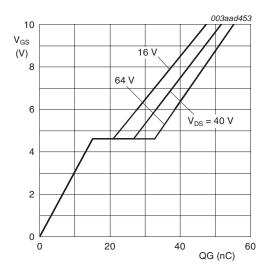
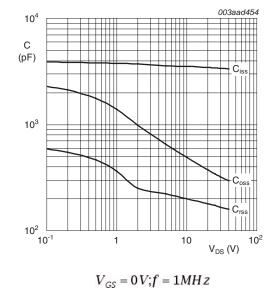


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25 \,^{\circ}C; I_D = 25A$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

Fig 15. Gate-source voltage as a function of gate charge; typical values

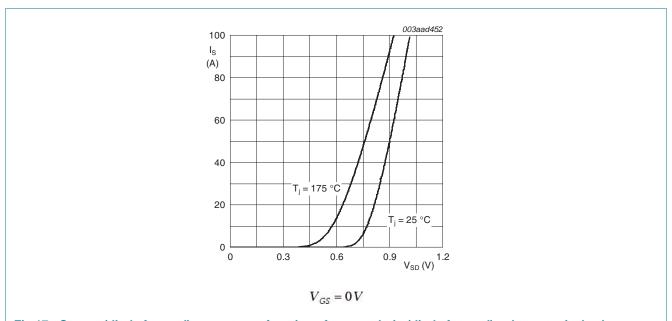
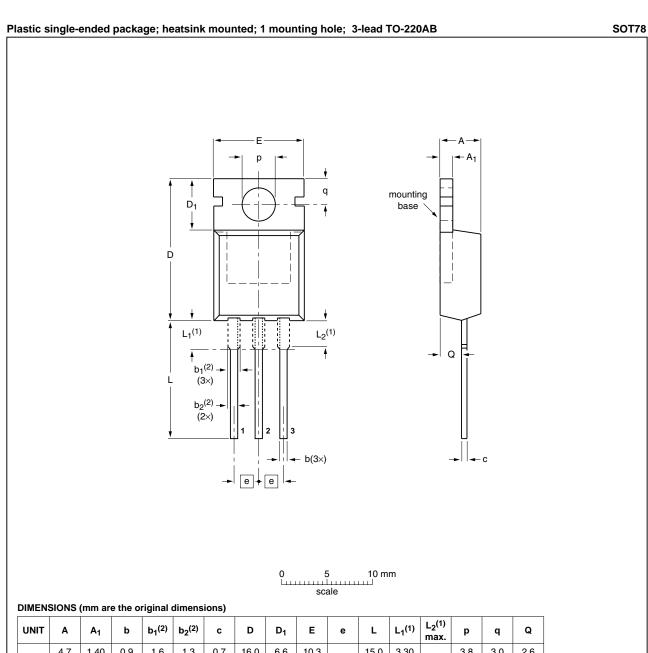


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### Package outline



UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EDEC JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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### 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80PS v.2	20101101	Product data sheet	-	PSMN8R7-80PS v.1
Modifications:	Status changed to Various changes			
	<ul> <li>Various changes</li> </ul>	to content.		
PSMN8R7-80PS v.1	20100129	Objective data sheet	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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## **PSMN8R7-80PS**

### **Nexperia**

#### N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220

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